mos integrated circuit $\mu \mathbf{PD4722}$

RS-232 LINE DRIVER/RECEIVER AT 3.3 V/5 V

The μ PD4722 is a high-breakdown voltage silicon gate CMOS line driver/receiver based on the EIA/TIA-232-E standard. The internal DC/DC converter can switch between multiple voltages, allowing it to operate with a single +3.3 V or +5 V power supply. It also provides standby function.

This IC incorporates 4 driver circuits and 4 receiver circuits. An RS-232 interface circuit can be easily configured by connecting 5 capacitors externally.

FEATURES

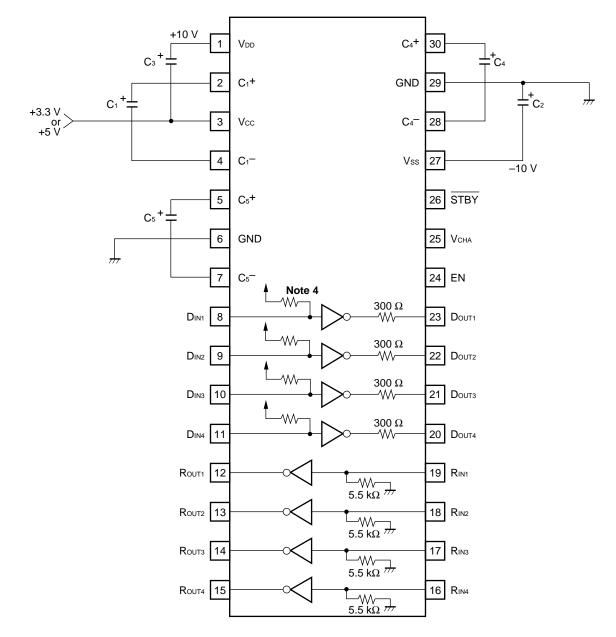
NEC

- · Conforms to EIA/TIA-232-E (former name, RS-232C) standards
- Selectable +3.3 V/+5 V single power supply (selected by VCHA pin)
- By setting the standby pin to a low level (standby mode), circuit current can be reduced. At such times, the driver output is in a high-impedance state.
- Even in the standby mode, 2 receiver circuits can operate as inverters without hysteresis width. The other 2 circuits are fixed at a high level.

ORDERING INFORMATION

Part number	Package
μPD4722GS-GJG	30-pin plastic SSOP (300 mil)

BLOCK DIAGRAM/PIN CONFIGURATION (TOP VIEW)



- Note 1. VDD and Vss are output pins stepped up internally. These pins should not be loaded directly.
 - **2**. Capacitors C₁ to C₅ with a breakdown voltage of 20 V or higher are recommended. And it is recommended to insert the capacitor that is 0.1 μ F to 1 μ F between Vcc and GND.
 - 3. If VCHA is kept low level (in 5 V mode), capacitor C_5 is not necessary.
 - 4. The pull-up resistors at driver input are active resistors.

Truth Table

Driver

STBY	Din	Dout	Remarks
L	×	Z	Standby mode (DC/DC converter is stopped)
н	L	Н	Space level output
н	Н	L	Mark level output

Receiver

STRV	STBY EN		RIN		DUT	Pomorko
5161	EN	R₃ to R₄	R1 to R2	R ₃ to R ₄	R1 to R2	H Standby mode 1 (DC/DC converter is stopped) H Standby mode 2 (DC/DC converter is stopped, R3 and R4 are operated)
L	L	×	×	н	Н	Standby mode 1 (DC/DC converter is stopped)
L	н	L	×	н	н	
L	н	н	×	L	Н	Standby mode 2 (DC/DC converter is stopped, R_3 and R_4 are operated)
н	×	L	-	Н		Mark level input
Н	×	ŀ	1	L	-	Space level input

3 V \leftrightarrow 5 V switching^{Note 5}

Vсна	Operating mode
L	5 V mode (double step-up)
н	3 V mode (3 times step-up)

H: high-level, L: low-level, Z: high-impedance, ×: H or L

Note 5. When switching V_{CHA}, standby mode must be selected ($\overline{\text{STBY}}$ = L).

ABSOLUTE MAXIMUM RATINGS (T_A = 25 $^{\circ}$ C)

Parameter	Symbol	Ratings	Unit
Supply Voltage (V _{CHA} = L)	Vcc	-0.5 to +7.0	V
Supply Voltage (V _{CHA} = H)	Vcc	-0.5 to +4.5	V
Driver Input Voltage	Din	-0.5 to Vcc +0.5	V
Receiver Input Voltage	Rin	-30.0 to +30.0	V
Control Input Voltage (STBY, VCHA, EN)	Vin	-0.5 to Vcc +0.5	V
Driver Output Voltage	Dout	-25.0 to +25.0 ^{Note 6}	V
Receiver Output Voltage	Rout	-0.5 to Vcc +0.5	V
Input Current (DIN, STBY, VCHA, EN)	lin	±20.0	mA
Operating Ambient Temperature	TA	-40 to +85	°C
Storage Temperature	Tstg	-55 to + 150	°C
Total Power Dissipation	Рт	0.5	W

Note 6. Pulse width = 1 ms, duty = 10 % MAX.

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage (V _{CHA} = L, 5 V mode)	Vcc	4.5	5.0	5.5	V
Supply Voltage (V _{CHA} = H, 3 V mode)	Vcc	3.0	3.3	3.6	V
High-Level Input Voltage (DIN)	Vін	2.0		Vcc	V
Low-Level Input Voltage (DIN)	VIL	0		0.8	V
High-Level Input Voltage (STBY, VCHA, EN)	Vін	2.4		Vcc	V
Low-Level Input Voltage (STBY, VCHA, EN)	VIL	0		0.6	V
Receiver Input Voltage	Rin	-30		+30	V
Operating Ambient Temperature	TA	-40		+85	°C
Capacitance of External Capacitor	Note 7	0.47		4.7	μF

Note 7. In low temperature (below 0 °C), the capacitance of electrolytic capacitor becomes lower. Therefore, set higher values when using in low temperature.

Concerning the wiring length between the capacitor and the IC, the shorter the better.

Capacitors with good frequency characteristics such as tantalum capacitors, laminated ceramic capacitors, and aluminum electrolytic capacitors for switching power supply are recommended for the external capacitors.

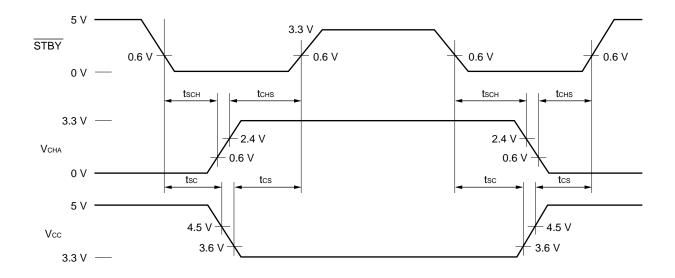
ELECTRICAL SPECIFICATIONS (TOTAL)

(UNLESS OTHERWISE SPECIFIED, $T_A = -40$ to +85 °C, C1 to C5 = 1 μ F)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current		V_{CC} = +3.3 V, No load, R _{IN} pin OPEN, STBY = H			MAX. 16 12 47 38 3 5 5 3 5 0.6 1 -1 10 10	mA
		V_{CC} = +5.0 V, No load, R _{IN} pin OPEN, STBY = H			12	mA
	Icc2	$ V_{CC} = +3.3 \text{ V}, \text{ RL} = 3 \frac{\text{k}\Omega \text{ (Dout)}, \text{ Din} = \text{GND}, } $			16 12 47 38 3 3 5 3 3 5 5 0.6 1 -1 10	mA
	1002	$ V_{CC} = +5.0 \ V, R_L = 3 \ k\Omega \ (D_{OUT}), \ D_{IN} = GND, \\ R_{IN}, \ R_{OUT} \ pin \ OPEN, \ \overline{STBY} = H $			38	mA
		V_{CC} = +3.3 V, No load, D _{IN} and R _{IN} pins are OPEN, \overline{STBY} = L, EN = L, TA = 25 °C		1	12 47 38 3 5 5 3 3 5 5 5 5 5 5 5 1 0.6 1 1 -1	μA
Circuit Current at Standby	Іссз	V_{CC} = +3.3 V, No load, DIN and RIN pins are OPEN, \overline{STBY} = L, EN = L		5		μA
(Standby Mode 1)	1003	Vcc = +5.0 V, No load, DIN and RIN pins are OPEN, $\overline{\text{STBY}}$ = L, EN = L, TA = 25 °C		2	5	μΑ
		V_{CC} = +5.0 V, No load, DIN and RIN pins are OPEN, $\overline{\text{STBY}}$ = L, EN = L		10		μΑ
		Vcc = +3.3 V, No load, DIN and RIN pins are OPEN, $\overline{\text{STBY}}$ = L, EN = H, TA = 25 °C		1	3	μA
Circuit Current at Standby		Vcc = +3.3 V, No load, D _{IN} and R _{IN} pins are OPEN, $\overline{\text{STBY}}$ = L, EN = H		5		μΑ
(Standby Mode 2)	Icc4	V _{CC} = +5.0 V, No load, D _{IN} and R _{IN} pins are OPEN, $\overline{\text{STBY}}$ = L, EN = H, T _A = 25 °C		2	5	μA
Standby Mode 1) Circuit Current at Standby (Standby Mode 2) High-Level Input Voltage -ow-Level Input Voltage High-Level Input Current -ow-Level Input Current nput Capacitance		V_{CC} = +5.0 V, No load, D _{IN} and R _{IN} pins are OPEN, STBY = L, EN = H		10		μA
High-Level Input Voltage	Vін	Vcc = +3.0 to +5.5 V, STBY, Vcна, EN pin	2.4			V
Low-Level Input Voltage	VIL	Vcc = +3.0 to +5.5 V, $\overline{\text{STBY}}$, Vcha, EN pin			0.6	V
High-Level Input Current	Ін	Vcc = +5.5 V, VI = 5.5 V, $\overline{\text{STBY}}$, Vcha, EN pin			1	μA
Low-Level Input Current	lı∟	$V_{CC} = +5.5 \text{ V}, \text{ VI} = 0 \text{ V}, \overline{\text{STBY}}, \text{ V}_{CHA}, \text{ EN pin}$			-1	μA
	0	Driver input and receiver input Vcc = +3.3 V, for GND, f = 1 MHz			10	pF
input Capacitance	Cin	Driver input and receiver input Vcc = +5.0 V, for GND, f = 1 MHz			10	pF
STBY — VCHA Time	tscн	V_{CC} = +3.0 to 5.5 V, $\overline{\text{STBY}}\downarrow \rightarrow V_{\text{CHA}}$ Note 8	1			μs
$V_{CHA} - \overline{STBY}$ Time	tснs	Vcc = +3.0 to 5.5 V, Vcha \rightarrow $\overline{\text{STBY}}$ ^, Note 8	1			μs
STBY — Vcc Time	tsc	V_{CC} = +3.0 to 5.5 V, $\overline{\text{STBY}}\downarrow\rightarrow\text{V}_{\text{CC}},$ Note 8	1			μs
$Vcc - \overline{STBY}$ Time	tcs	Vcc = +3.0 to 5.5 V, Vcc → $\overline{\text{STBY}}$ ↑, Note 8	1			μs

* The TYP. values are for reference at T_A = 25 °C.

Note 8. Measuring point



ELECTRICAL SPECIFICATIONS (DRIVER)

(UNLESS OTHERWISE SPECIFIED, $T_A = -40$ to +85 °C, C1 to C5 = 1 μ F)

3 V mode (u	unless otherwise	specified, Vc	на = H, Vcc =	= 3.0 to 3.6 V)
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Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Low-Level Input Voltage	VIL				0.8	V
High-Level Input Voltage	VIH		2.0			V
Low-Level Input Current	lı∟	Vcc = +3.6 V, VI = 0 V			-25	μΑ
High-Level Input Current	Ін	Vcc = +3.6 V, VI = 3.6 V			1.0	μΑ
		Vcc = +3.3 V, RL = ∞, TA = 25 °C		±9.5		V
Output Voltage	Vdo	Vcc = +3.3 V, R _L = 3 k Ω , T _A = T _{opt}	±5.0	±6.0		V
	ent IIH $V_{CC} = +3.6 V, V_{I} = 3.6 V$ 1.0 $V_{CC} = +3.3 V, R_{L} = \infty, T_{A} = 25 ^{\circ}C$ ± 9.5 $V_{CC} = +3.3 V, R_{L} = 3 k\Omega, T_{A} = T_{opt}$ $\pm 5.0 \pm 6.0$ $V_{CC} = +3.0 V, R_{L} = 3 k\Omega, T_{A} = +25 ^{\circ}C$ ± 5.0 Current Isc $V_{CC} = +3.3 V, \text{ for GND}$ ± 40 $C_{L} = 10 \text{ pF}, R_{L} = 3 \text{ to } 7 \text{ k}\Omega$ 3.0 30 $C_{L} = 2 500 \text{ pF}, R_{L} = 3 \text{ to } 7 \text{ k}\Omega$ 3.0 30 me ^{Note 9} $\frac{t_{PHL}}{t_{PLH}}$ $R_{L} = 3 k\Omega, C_{L} = 2 500 \text{ pF}$ 2.5		V			
Output Short-Circuit Current	Isc	Vcc = +3.3 V, for GND			±40	mA
Slew-RateNote 9	CD	$C_L = 10 \text{ pF}, R_L = 3 \text{ to } 7 \text{ k}\Omega$	3.0		30	V/µs
Slew-Kale	JR	C_L = 2 500 pF, R_L = 3 to 7 k Ω	2.0 0.8 2.0 -25 1.0 μ 2.0 1.0 1.0 μ 2.0 1.0 1.0 μ 2.5° C ± 9.5 $T_{A} = T_{opt}$ ± 5.0 ± 6.0 $T_{A} = +25^{\circ}$ C ± 5.0 ± 40 n Ω 3.0 30 V_{A} 1 3.0 30 V_{A} 300 2.5 μ 300 4 10 μ γ Note 10 4 10 μ	V/µs		
Propagation Delay Time ^{Note 9}		$R_L = 3 k\Omega, C_L = 2 500 pF$		2.5		μs
Output Resistor	Ro	$V_{CC} = V_{DD} = V_{SS} = 0 V$ $V_{OUT} = \pm 2 V$	300			Ω
Standby Output Transfer Time	tdaz	$R_{L} = 3 \text{ k}\Omega, C_{L} = 2 \text{ 500 pF}, \text{Note 10}$		4	10	μs
Standby Output Transfer Time	tdza	$R_{L} = 3 \ k\Omega, \ C_{L} = 2 \ 500 \ pF, Note \ 10$		1	3	ms
Power-On Output Transfer Time	t pra	$R_L = 3 \ k\Omega, \ C_L = 2 \ 500 \ pF,$ Note 11		1	3	ms

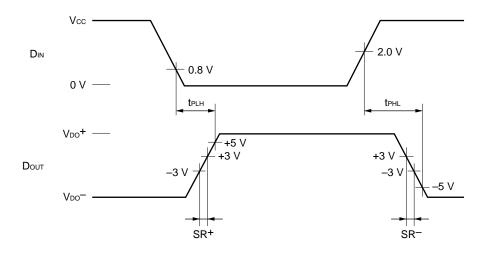
* The TYP. values are for reference at T_{A} = 25 °C.

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Low-Level Input Voltage	VIL				0.8	V
High-Level Input Voltage	Vін		2.0			V
Low-Level Input Current	lı∟	$Vcc = +5.5 V, V_1 = 0 V$			-40	μΑ
High-Level Input Current	Ін	Vcc = +5.5 V, VI = 5.5 V			1.0	μΑ
		V_{CC} = +5.0 V, R_L = ∞ , T_A = 25 °C		±9.7		V
Output Voltage	Vdo	Vcc = +5.0 V, R _L = 3 k Ω , T _A = T _{opt}	±6.0			V
		Vcc = +4.5 V, R _L = 3 k Ω , T _A = T _{opt}	±5.0			V
Output Short-Circuit Current	Isc	Vcc = +5.0 V, for GND			±40	mA
Slew-Rate ^{Note 9}	SR	C_L = 10 pF, R_L = 3 to 7 k Ω	4.0		30	V/µs
	SK	$C_L = 2500 \text{ pF}, R_L = 3 \text{ to } 7 \text{ k}\Omega$	4.0		30	V/µs
Propagation Delay Time ^{Note 9}	tрнг tргн	$R_L = 3 \text{ k}\Omega, C_L = 2 \text{ 500 pF}$		2		μs
Output Resistor	Ro	$V_{CC} = V_{DD} = V_{SS} = 0 V$ $V_{OUT} = \pm 2 V$	300			Ω
Standby Output Transfer Time	tdaz	$R_L = 3 \ k\Omega, \ C_L = 2 \ 500 \ pF, Note \ 10$		4	10	μs
Standby Output Transfer Time	t dza	$R_L = 3 \ k\Omega, \ C_L = 2 \ 500 \ pF, Note \ 10$		0.5	1	ms
Power-On Output Transfer Time	t pra	$R_L = 3 \text{ k}\Omega, C_L = 2 \text{ 500 pF}, \text{Note 12}$		0.5	1	ms

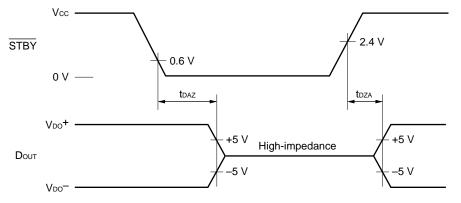
5 V mode (unless	otherwise specifie	ed, VCHA = L, VCC = +	5.0 V ± 10 %)
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* The TYP. values are for reference at TA = 25 °C.

Note 9. Measuring point

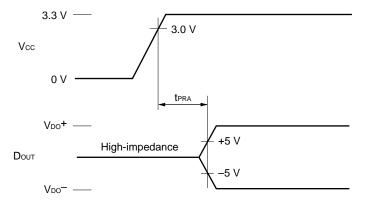


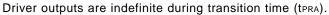
Note 10. Measuring point



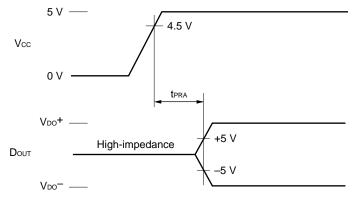
Driver outputs are indefinite during transition time (tDZA).

Note 11. Measuring point





Note 12. Measuring point



Driver outputs are indefinite during transition time (tpra).

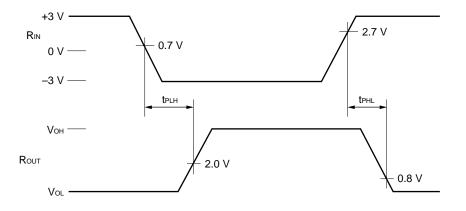
ELECTRICAL SPECIFICATIONS (RECEIVER)

(UNLESS OTHERWISE SPECIFIED, Vcc = 3.0 to 5.5 V, TA = -40 to +85 °C, C1 to C5 = 1 μ F)

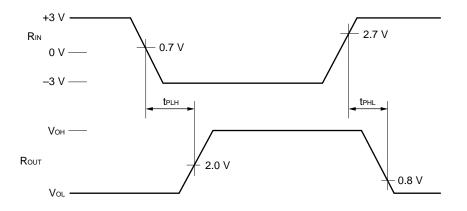
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Low-Level Output Voltage	Vol1	lout = 4 mA, $\overline{\text{STBY}}$ = H			0.4	V
High-Level Output Voltage	Vон1	lout = -4 mA, STBY = Η	Vcc – 0.4			V
Low-Level Output Voltage	Vol2	louτ = 4 mA, STBY = L			0.5	V
High-Level Output Voltage	Vон2	lout = $-4 \text{ mA}, \overline{\text{STBY}} = L$	Vcc – 0.5			V
Propagation Delay Time (STBY = H)	tрні tplh	$\label{eq:Rindown} \begin{split} R_{\text{IN}} & \rightarrow R_{\text{OUT}}, \ C_{\text{L}} = 150 \ \text{pF} \\ V_{\text{CC}} = +3.0 \ \text{V}, \\ \end{split} $		0.2		μs
Propagation Delay Time (STBY = L)	tрні tplh	$\label{eq:Rindown} \begin{split} R_{\text{IN}} & \rightarrow R_{\text{OUT}}, \ C_{\text{L}} = 150 \ \text{pF} \\ V_{\text{CC}} = +3.0 \ \text{V}, \\ \end{split} $		0.1		μs
Propagation Delay Time (STBY = L)	tрна tран	$\label{eq:expectation} \begin{split} EN &\to Rout, \ CL = 150 \ pF \\ Vcc = +3.0 \ V, & Note 15 \end{split}$		100	300	ns
Input Resistor	Ri		3	5.5	7	kΩ
Input Pin Open Voltage	Vio				0.5	V
	Pin Open Voltage Vio	Vcc = +3.0 to +5.5 V	1.7	2.3	2.7	V
Input Threshold ($\overline{STBY} = H$)	VIL	Vcc = +3.0 to +5.5 V	0.7	1.1	1.7	V
	Vн	Vcc = +3.0 to +5.5 V (Hysteresis width)	0.5	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	V	
Input Threshold	Vін	Vcc = +3.0 to +5.5 V, RIN3, RIN4	2.7	1.5		V
$(\overline{\text{STBY}} = L, EN = H)$	VIL	Vcc = +3.0 to +5.5 V, RIN3, RIN4	+3.0 V, Note 13 0.2 Rout, CL = 150 pF 0.1 Rout, CL = 150 pF 100 *3.0 V, Note 14 100 Rout, CL = 150 pF 100 *3.0 V, Note 15 100 3 5.5 *3.0 to +5.5 V 1.7 *3.0 to +5.5 V 0.7 *3.0 to +5.5 V 0.7 *3.0 to +5.5 V (Hysteresis width) 0.5 *3.0 to +5.5 V, RIN3, RIN4 2.7 *3.0 to +5.5 V, RIN3, RIN4 1.5 *3.0 to +5.5 V, RIN3, RIN4 0.2 *3.0 to +5.5 V, RIN3, RIN4 1.5 *3.0 to +5.5 V, RIN3, RIN4 1.5	V		
Standby Output Transfer Time	tdah	Note 16		0.2	3	μs
Standby Output Transfer Time	tour	V _{CHA} = H (3 V mode) ^{Note 16}		0.6	3	ms
	t dha	V _{CHA} = L (5 V mode) ^{Note 16}		100 300 5.5 7 0.5 0.5 2.3 2.7 1.1 1.7 1.2 1.8 1.5 0.7 0.2 3 0.6 3 0.3 1	ms	
Denver On Decet Deleger Time		VCHA = H (3 V mode) ^{Note 17}		1	3	ms
Power-On Reset Release Time	t pra	V _{CHA} = L (5 V mode) ^{Note 18}		0.5	1	ms

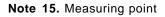
* The TYP. values are for reference at T_A = 25 °C.

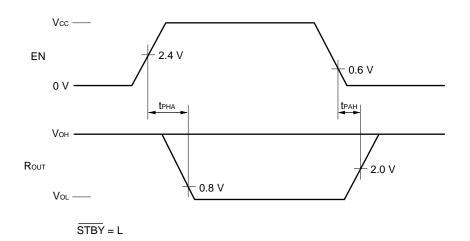
Note 13. Measuring point



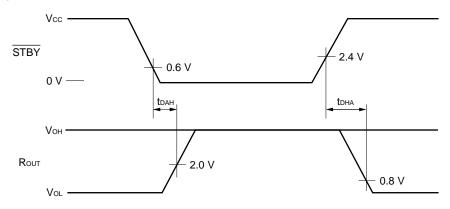
Note 14. Measuring point





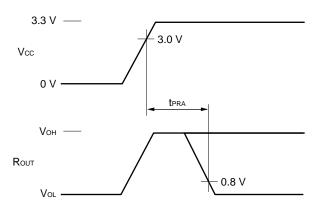


Note 16. Measuring point



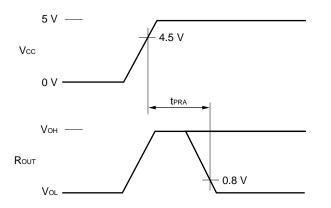
Receiver outputs are indefinite during transition time (tDHA).

Note 17. Measuring point



Receiver outputs are indefinite during reset release time (tPRA).

Note 18. Measuring point



Receiver outputs are indefinite during reset release time (tPRA).

REFERENCE MATERIAL

- IC PACKAGE MANUAL (C10943X)
- NEC SEMICONDUCTOR DEVICE RELIABILITY/QUALITY (IEI-1212)

RECOMMENDED SOLDERING CONDITIONS

The following conditions (See table below) must be met when soldering this product.

Please consult with our sales offices in case other soldering process is used, or in case soldering is done under different conditions.

TYPES OF SURFACE MOUNT DEVICE

For more details, refer to our document "SMT MANUAL" (C10535E).

μ PD4722 GS-GJG

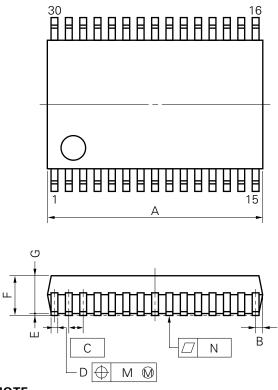
Soldering process	Soldering conditions	Symbol
Infrared ray reflow	Peak package's surface temperature: 230 °C or below, Reflow time: 30 seconds or below (210 °C or higher), Number of reflow process: 2, Exposure limit*: None	IR30-00-2
VPS	Peak package's surface temperature: 215 °C or below, Reflow time: 40 seconds or below (200 °C or higher), Number of reflow process: 2, Exposure limit*: None	VP15-00-2
Wave soldering	Solder temperature: 260 °C or below, Flow time: 10 seconds or below, Number of flow process: 1, Exposure limit*: None	WS60-00-1
Partial heating method	Terminal temperature: 300 °C or below, Flow time: 10 seconds or below, Exposure limit*: None	0

* Exposure limit before soldering after dry-pack package is opened. Storage conditions: 25 °C and relative humidity at 65 % or less.

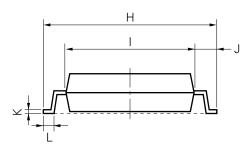
Note Do not apply more than a single process at once, except for "Partial heating method"

PACKAGE DRAWINGS

30 PIN PLASTIC SHRINK SOP (300 mil)



detail of lead end



P30GS-65-300B-1

Each lead centerline is located within 0.10 mm (0.004 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
А	10.11 MAX.	0.398 MAX.
В	0.51 MAX.	0.020 MAX.
С	0.65 (T.P.)	0.026 (T.P.)
D	$0.30_{-0.05}^{+0.10}$	$0.012\substack{+0.004\\-0.003}$
E	0.125±0.075	0.005±0.003
F	2.0 MAX.	0.079 MAX.
G	1.7±0.1	0.067±0.004
Н	8.1±0.2	0.319±0.008
I	6.1±0.2	0.240±0.008
J	1.0±0.2	0.039+0.009
К	$0.15^{+0.10}_{-0.05}$	$0.006^{+0.004}_{-0.002}$
L	0.5±0.2	0.020+0.008
М	0.10	0.004
Ν	0.10	0.004

[MEMO]

[MEMO]

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NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

- Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
- Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
- Specific: Aircrafts, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.

Anti-radioactive design is not implemented in this product.